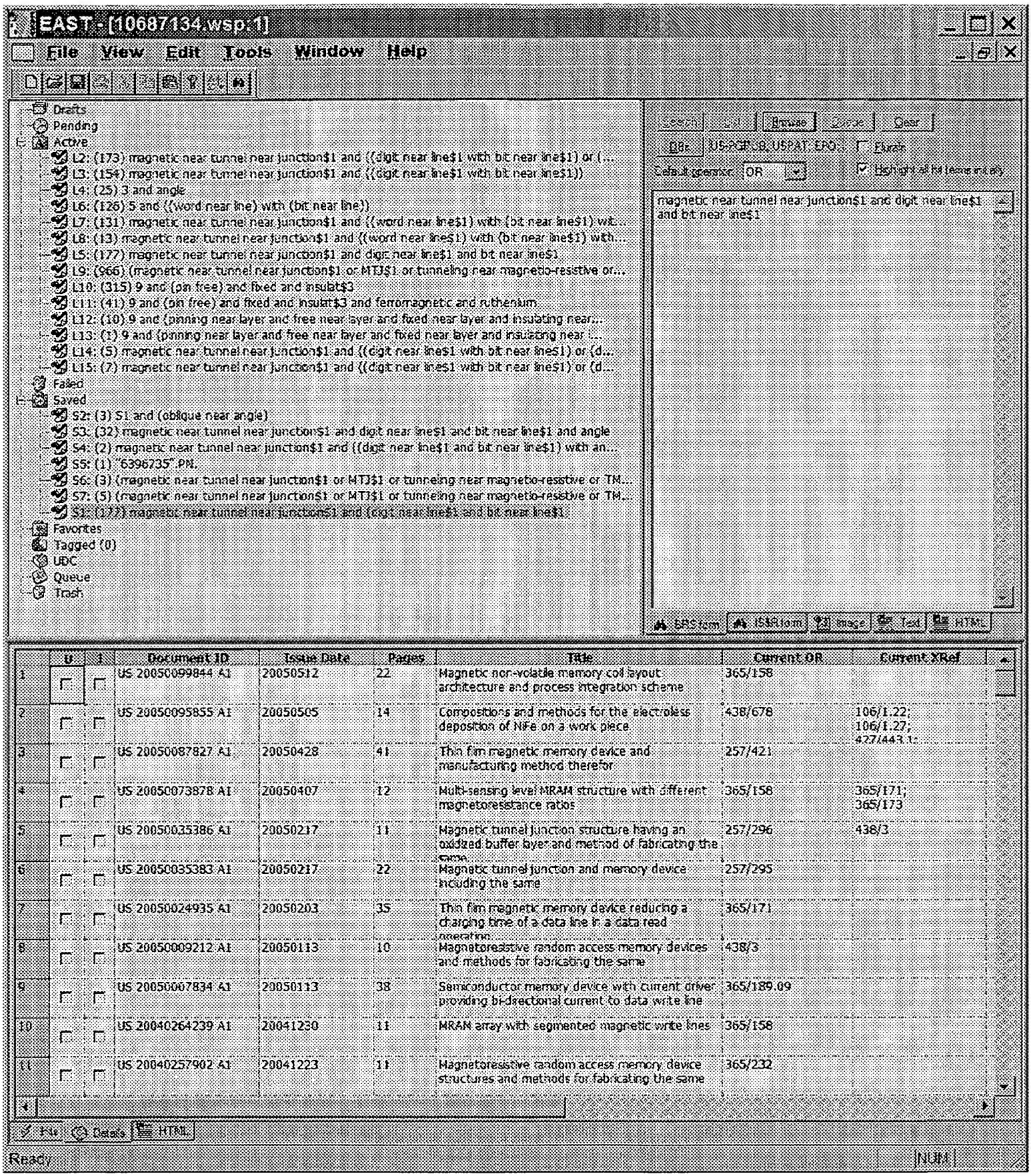
EAST - [10687134.wsp 1]
File View Edit Tools Window Help
Drafts
Pending
Active
L2: (173) magnetic near tunnel near junction$1 and ((digit near line$1 with bit near line$1) or (...
L3: (154) magnetic near tunnel near junction$1 and ((digit near line$1 with bit near line$1))
L4: (25) 3 and angle
L6: (126) 5 and ((word near line) with (bit near line))
L7: (131) magnetic near tunnel near junction$1 and ((word near line$1) with (bit near line$1) wit...
L8: (13) magnetic near tunnel near junction$1 and ((word near line$1) with (bit near line$1) with...
L5: (177) magnetic near tunnel near junction$1 and digit near line$1 and bit near line$1
L9: (966) (magnetic near tunnel near junction$1 or MTJ$1 or tunneling near magnetic-resistive or...
L10: (315) 9 and (pin free) and fixed and insulat$3
L11: (41) 9 and (pin free) and fixed and insulat$3 and ferromagnetic and ruthenium
L12: (10) 9 and (pinning near layer and free near layer and fixed near layer and insulating near...
L13: (1) 9 and (pinning near layer and free near layer and fixed near layer and insulating near l...
L14: (5) magnetic near tunnel near junction$1 and ((digit near line$1 with bit near line$1) or (d...
L15: (7) magnetic near tunnel near junction$1 and ((digit near line$1 with bit near line$1) or (d...
Failed
Saved
S2: (3) S1 and (oblique near angle)
S3: (32) magnetic near tunnel near junction$1 and digit near line$1 and bit near line$1 and angle
S4: (2) magnetic near tunnel near junction$1 and ((digit near line$1 and bit near line$1) with an...
S5: (1) "6396735".PN.
S6: (3) (magnetic near tunnel near junction$1 or MTJ$1 or tunneling near magnetic-resistive or TM...
S7: (5) (magnetic near tunnel near junction$1 or MTJ$1 or tunneling near magnetic-resistive or TM...
S1: (177) magnetic near tunnel near junction$1 and (digit near line$1 and bit near line$1
Favorites
Tagged (0)
UDC
Queue
Trash
Search Edit Browse Clear Clear
DBs US-PGPUB, USPAT, EPO, ... Plural
Default operator: OR Highlight all hit terms in text
magnetic near tunnel near junction$1 and digit near line$1 and bit near line$1
ERS form ISR form Image Text HTML
U I Document ID Issue Date Pages Title Current OR Current XRef
1 US 20050099844 A1 20050512 22 Magnetic non-volatile memory cell layout architecture and process integration scheme 365/158
2 US 20050095855 A1 20050505 14 Compositions and methods for the electroless deposition of NiFe on a work piece 438/678 106/1.22; 106/1.27; 427/443.1;
3 US 20050087827 A1 20050428 41 Thin film magnetic memory device and manufacturing method therefor 257/421
4 US 20050073878 A1 20050407 12 Multi-sensing level MRAM structure with different magnetoresistance ratios 365/158 365/171; 365/173
5 US 20050035386 A1 20050217 11 Magnetic tunnel junction structure having an oxidized buffer layer and method of fabricating the same 257/296 438/3
6 US 20050035383 A1 20050217 22 Magnetic tunnel junction and memory device including the same 257/295
7 US 20050024935 A1 20050203 35 Thin film magnetic memory device reducing a charging time of a data line in a data read operation 365/171
8 US 20050009212 A1 20050113 10 Magnetoresistive random access memory devices and methods for fabricating the same 438/3
9 US 20050007834 A1 20050113 38 Semiconductor memory device with current driver providing bi-directional current to data write line 365/189.09
10 US 20040264239 A1 20041230 11 MRAM array with segmented magnetic write lines 365/158
11 US 20040257902 A1 20041223 11 Magnetoresistive random access memory device structures and methods for fabricating the same 365/232
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